

Type	L #	Hits	Search Text	DBs	Time Stamp	Err	Err	Err	Err	Err
						Count	Count	Count	Count	Count
1	BRS	L3	3573 ((silicon adj on adj insulat\$3) SOI)	USPAT	2000/09/21 16:47	0	0	0	0	0
2	BRS	L4	1418 3 and bond\$3	USPAT	2000/09/21 16:47	0	0	0	0	0
3	BRS	L5	525 3 and join\$3	USPAT	2000/09/21 16:48	0	0	0	0	0
4	BRS	L7	1670 4 5	USPAT	2000/09/21 16:49	0	0	0	0	0
5	BRS	L8	761 7 and (oxidiz\$3)	USPAT	2000/09/21 16:53	0	0	0	0	0
6	BRS	L9	3 8 and (mono adj crystal\$6 adj silicon)	USPAT	2000/09/21 16:55	0	0	0	0	0
7	BRS	L10	647 8 and (implant\$3 dop\$4)	USPAT	2000/09/21 16:57	0	0	0	0	0
8	BRS	L11	330 10 and (substrate with oxidiz\$3)	USPAT	2000/09/21 19:44	0	0	0	0	0

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Date: 09/21/2000

Time: 20:40

Type	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Ro re in ts
1	BRS 444663	substrate semiconductor wafer	USPAT	2000/09/14 11:00	0	0
2	BRS 128507	(substrate semiconductor wafer) and (insulat\$3)	USPAT	2000/09/14 11:07	0	0
3	BRS 0	1 and (dielectric)	USPAT	2000/09/14 11:07	0	0
4	BRS 239704	((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)	USPAT	2000/09/14 13:50	0	0
5	BRS 24527	((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and polysilicon	USPAT	2000/09/14 13:51	0	0
6	BRS 7758	((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and (single adj crystal\$6 adj silicon)	USPAT	2000/09/14 13:55	0	0
7	BRS 33	((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and (mono adj crystal\$3 adj silicon)	USPAT	2000/09/14 14:00	0	0
8	BRS 10877	((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and (amorphous adj silicon)	USPAT	2000/09/14 14:01	0	0

ID	Type	Hits	Search Text	DBs	Time Stamp	Co mm en	re fo	ti ts	n i	t i	o
9	BRS	35125	(((substrate semiconductor wafer) and (dielectric insulator\$3 oxide)) and ((substrate semiconductor wafer) and (dielectric insulator\$3 oxide)) and (mono adj crystal\$3 adj silicon)) (((substrate semiconductor wafer) and (dielectric insulator\$3 oxide)) and (single adj crystal\$6 adj silicon)) (((substrate semiconductor wafer) and (dielectric insulator\$3 oxide)) and polysilicon)	USPAT	2000/09/14 14:02	0					
10	BRS	14046	(((substrate semiconductor wafer) and (dielectric insulator\$3 oxide)) and (amorphous adj silicon)) (((substrate semiconductor wafer) and (dielectric insulator\$3 oxide)) and (mono adj crystal\$3 adj silicon)) (((substrate semiconductor wafer) and (dielectric insulator\$3 oxide)) and (single adj crystal\$6 adj silicon)) (((substrate semiconductor wafer) and (dielectric insulator\$3 oxide)) and polysilicon)) and implant\$3	USPAT	2000/09/14 14:04	0					

Type	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Do r e n t i s	E r o r e n t i s
12	BRS 3248	(((((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and (amorphous adj silicon)) (((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and (mono adj crystal\$3 adj silicon)) (((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and (single adj crystal\$6 adj silicon)) (((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and polysilicon)) and implant\$3) and (nitrogen)	USPAT	2000/09/14 14:18	0	0	0

E	R	H	O	R	E	C	o	D	r	m	e	r	n	i	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t	o	t	s	i	t</